Octal D-Type Flip-Flop with 3-State Output

The MC74VHC374 is an advanced high speed CMOS octal flip-flip with 3-state output fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

This 8-bit D-type flip-flop is controlled by a clock input and an output enable input. When the output enable input is high, the eight outputs are in a high impedance state.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7V, allowing the interface of 5V systems to 3V systems.

Features

- High Speed: $f_{max} = 185 \text{ MHz}$ (Typ) at $V_{CC} = 5 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4 \mu A \text{ (Max)}$ at $T_A = 25^{\circ}\text{C}$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: V_{OLP} = 0.9 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 266 FETs or 66.5 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant



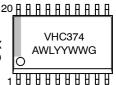
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MARKING DIAGRAMS

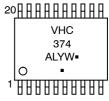


SOIC-20 **DW SUFFIX** CASE 751D





TSSOP-20 **DT SUFFIX** CASE 948E





SOEIAJ-20 **M SUFFIX CASE 967** lo

VHC374 **AWLYWWG**

= Specific Device Code VHC374 = Assembly Location = Wafer Lot

WL, L = Year WW, W = Work Week G or ■ = Pb-Free Package (Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHC374DWR2G	SOIC-20	1000 Units/Reel
MC74VHC374DTR2G	TSSOP-20	2500 Units/T&R
MC74VHC374MELG	SOEIAJ-20	2000 Units/Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

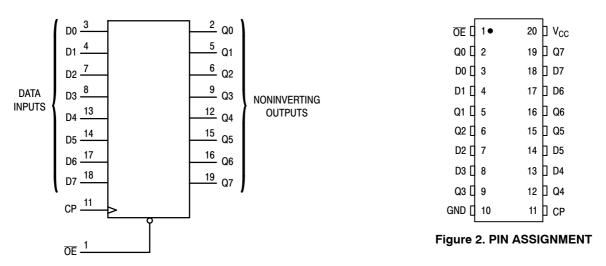


Figure 1. LOGIC DIAGRAM

FUNCTION TABLE

	INPUTS	ОИТРИТ	
ŌĒ	СР	D	q
	., H, \.	H L X	H L No Change

MAXIMUM RATINGS*

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		- 0.5 to + 7.0	V
V _{in}	DC Input Voltage		- 0.5 to + 7.0	V
V _{out}	DC Output Voltage	$-$ 0.5 to V_{CC} + 0.5	V	
I _{IK}	Input Diode Current	- 20	mA	
I _{OK}	Output Diode Current	± 20	mA	
l _{out}	DC Output Current, per Pin		± 25	mA
Icc	DC Supply Current, V _{CC} and GND I	Pins	± 75	mA
P _D		SOIC Packages† SSOP Package†	500 450	mW
T _{stg}	Storage Temperature		- 65 to + 150	°C

^{*} Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	5.5	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage	0	V_{CC}	V
T _A	Operating Temperature	- 40	+ 85	°C
t _r , t _f	Input Rise and Fall Time $ V_{CC} = 3.3 V_{CC} = 5.0 V_{CC} \label{eq:VCC} $	0	100 20	ns/V

DC ELECTRICAL CHARACTERISTICS

			V_{CC} $T_A = 25^{\circ}C$ $T_A = -40 \text{ to}$	T _A = 25°C		0 to 85°C			
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 to 5.5	1.50 V _{CC} x 0.7			1.50 V _{CC} x 0.7		V
V _{IL}	Maximum Low-Level Input Voltage		2.0 3.0 to 5.5			0.50 V _{CC} x 0.3		0.50 V _{CC} x 0.3	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V
		$V_{in} = V_{IH} \text{ or } V_{IL} \\ I_{OH} = - \text{ 4mA} \\ I_{OH} = - \text{ 8mA}$	3.0 4.5	2.58 3.94			2.48 3.80		
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4mA$ $I_{OL} = 8mA$	3.0 4.5			0.36 0.36		0.44 0.44	

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

[†]Derating — SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

DC ELECTRICAL CHARACTERISTICS

			v _{cc}	V _{CC} T _A = 25°C			T _A = - 40		
Symbol	Parameter	Test Conditions	v	Min	Тур	Max	Min	Max	Unit
l _{in}	Maximum Input Leakage Current	V _{in} = 5.5V or GND	0 to 5.5			± 0.1		± 1.0	μА
I _{OZ}	Maximum Three-State Leakage Current	V _{in} = V _{IL} or V _{IH} V _{out} = V _{CC} or GND	5.5			± 0.25		± 2.5	μА
I _{CC}	Maximum Quiescent Supply Current	V _{in} = V _{CC} or GND	5.5			4.0		40.0	μА

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

					T _A = 25°C		T _A = -4	0 to 85°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Unit
f _{max}	Maximum Clock Frequency (50% Duty Cycle)	$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15pF$ $C_L = 50pF$	80 55	130 85		70 50		ns
		$V_{CC} = 5.0 \pm 0.5 V$	$C_L = 15pF$ $C_L = 50pF$	130 85	185 120		110 75		
t _{PLH} , t _{PHL}	Maximum Propagation Delay, CP to Q	$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15pF$ $C_L = 50pF$		8.1 10.6	12.7 16.2	1.0 1.0	15.0 18.5	ns
		$V_{CC} = 5.0 \pm 0.5 V$	$C_L = 15pF$ $C_L = 50pF$		5.4 6.9	8.1 10.1	1.0 1.0	9.5 11.5	
t _{PZL} , t _{PZH}	Output Enable Time, OE to Q	$\begin{aligned} V_{CC} &= 3.3 \pm 0.3 V \\ R_L &= 1 k \Omega \end{aligned}$			7.1 9.6	11.0 14.5	1.0 1.0	13.0 16.5	ns
		$V_{CC} = 5.0 \pm 0.5V$ $R_L = 1k\Omega$	$C_L = 15pF$ $C_L = 50pF$		5.1 6.6	7.6 9.6	1.0 1.0	9.0 11.0	
t _{PLZ} , t _{PHZ}	Output Disable Time, OE to Q	$\begin{aligned} V_{CC} &= 3.3 \pm 0.3 V \\ R_L &= 1 k \Omega \end{aligned}$	C _L = 50pF		10.2	14.0	1.0	16.0	ns
		$\begin{aligned} V_{CC} &= 5.0 \pm 0.5 V \\ R_L &= 1 k \Omega \end{aligned}$	C _L = 50pF		6.1	8.8	1.0	10.0	
t _{OSLH} , t _{OSHL}	Output to Output Skew	V _{CC} = 3.3 ± 0.3V (Note 1)	C _L = 50pF			1.5		1.5	ns
		V _{CC} = 5.0 ± 0.5V (Note 1)	C _L = 50pF			1.0		1.0	ns
C _{in}	Maximum Input Capacitance				4	10		10	pF
C _{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)				6				pF

		Typical @ 25°C, V _{CC} = 5.0V	
C_{PD}	Power Dissipation Capacitance (Note 2)	32	pF

Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|.
 C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per flip-flop). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V)

		T _A = 25°C		
Symbol	Parameter	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.6	0.9	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}		- 0.9	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

TIMING REQUIREMENTS (Input $t_r = t_f = 3.0 \text{ns}$)

			T _A = 25°C		T _A = - 40 to 85°C	
Symbol	Parameter	Test Conditions	Тур	Limit	Limit	Unit
t _w	Minimum Pulse Width, CP	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \pm 0.5 \text{ V}$		5.0 5.0	5.5 5.0	ns
t _{su}	Minimum Setup Time, D to CP	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \pm 0.5 \text{ V}$		4.5 3.0	4.5 3.0	ns
t _h	Minimum Hold Time, D to CP	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \pm 0.5 \text{ V}$		2.0 2.0	2.0 2.0	ns
t _r , t _f	Maximum Input Rise and Fall Times	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \pm 0.5 \text{ V}$				ns

SWITCHING WAVEFORMS

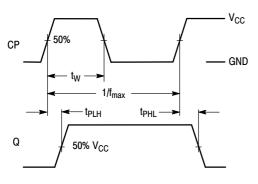


Figure 3.

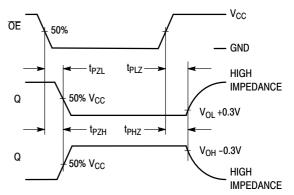


Figure 4.

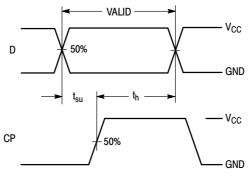
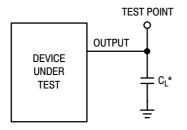
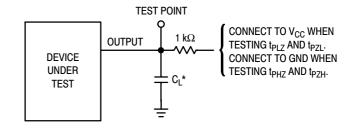


Figure 5.

TEST CIRCUITS





*Includes all probe and jig capacitance

*Includes all probe and jig capacitance

Figure 6.

Figure 7.

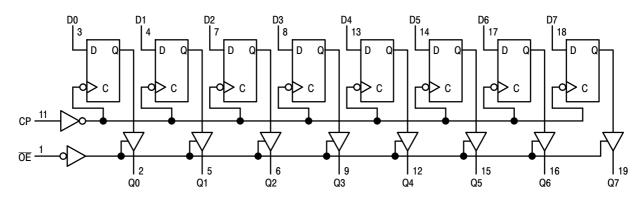


Figure 8. EXPANDED LOGIC DIAGRAM

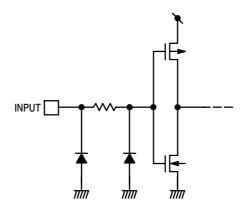
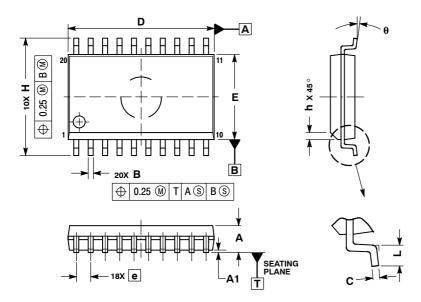


Figure 9. INPUT EQUIVALENT CIRCUIT

PACKAGE DIMENSIONS

SOIC-20 **DW SUFFIX** CASE 751D-05 ISSUE G



NOTES:

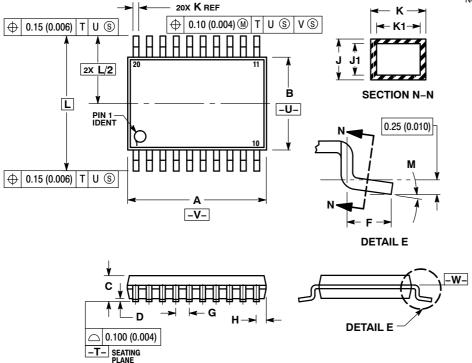
- NOTES:

 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS					
DIM	MIN	MAX				
Α	2.35	2.65				
A1	0.10	0.25				
В	0.35	0.49				
С	0.23	0.32				
D	12.65	12.95				
E	7.40	7.60				
е	1.27	BSC				
Н	10.05	10.55				
h	0.25	0.75				
L	0.50	0.90				
A	0 °	7 °				

PACKAGE DIMENSIONS

TSSOP-20 CASE 948E-02 **ISSUE C**



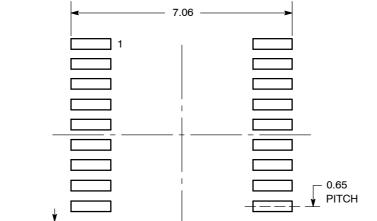
16X 0.36

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

- MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE
- DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE W-.

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252	BSC	
M	0°	8°	0°	8°	



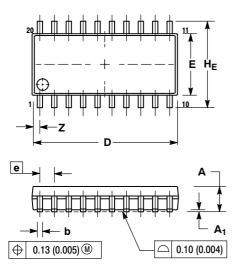
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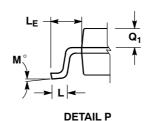
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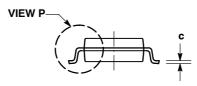
DIMENSIONS: MILLIMETERS

PACKAGE DIMENSIONS

SOEIAJ-20 CASE 967-01 **ISSUE A**







NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.
- B. DIMENSIONS D AND E DO NOT INCLUDE
 MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY
- 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003)
 TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.
 DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE
 BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.15	0.25	0.006	0.010
D	12.35	12.80	0.486	0.504
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q_1	0.70	0.90	0.028	0.035
Z		0.81		0.032

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